



ECH8668

Power MOSFET

20V, 7.5A, 17mΩ, -20V, -5A, 38mΩ, Complementary Dual ECH8

ON Semiconductor®

<http://onsemi.com>

Features

- The ECH8668 incorporates an N-channel MOSFET and a P-channel MOSFET that feature low ON-resistance and high-speed switching , thereby enabling high-density mounting
- 1.8V drive
- Halogen free compliance
- Protection diode in

Specifications

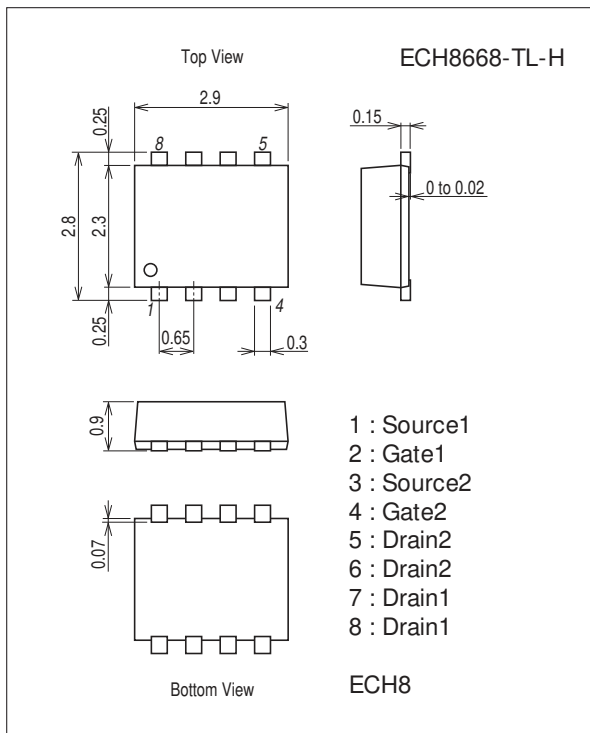
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	N-channel	P-channel	Unit
Drain-to-Source Voltage	V _{DSS}		20	-20	V
Gate-to-Source Voltage	V _{GSS}		±10	±10	V
Drain Current (DC)	I _D		7.5	-5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	40	-40	A
Allowable Power Dissipation	P _D	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	1.3		W
Total Dissipation	P _T	When mounted on ceramic substrate (900mm ² ×0.8mm)	1.5		W
Channel Temperature	T _{ch}		150		°C
Storage Temperature	T _{stg}		-55 to +150		°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

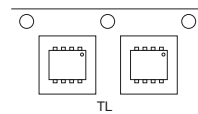
unit : mm (typ)
7011A-001



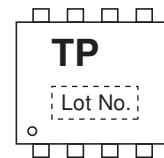
Product & Package Information

- Package : ECH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

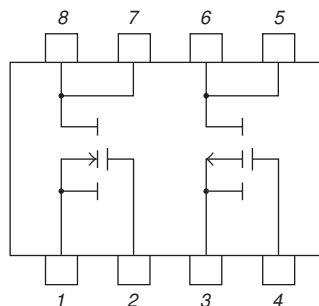
Packing Type : TL



Marking



Electrical Connection



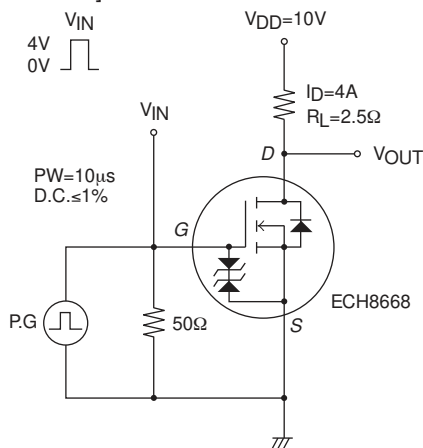
ECH8668

Electrical Characteristics at Ta=25°C

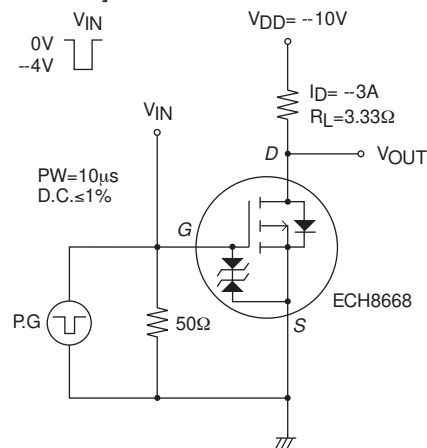
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[N-channel]						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1\text{mA}, V_{GS}=0\text{V}$	20			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20\text{V}, V_{GS}=0\text{V}$			1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8\text{V}, V_{DS}=0\text{V}$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10\text{V}, I_D=1\text{mA}$	0.5		1.3	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10\text{V}, I_D=4\text{A}$	4.2	7		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=4\text{A}, V_{GS}=4.5\text{V}$		13	17	$\text{m}\Omega$
	$R_{DS(on)2}$	$I_D=2\text{A}, V_{GS}=2.5\text{V}$		18	26	$\text{m}\Omega$
	$R_{DS(on)3}$	$I_D=0.5\text{A}, V_{GS}=1.8\text{V}$		30	48	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{DS}=10\text{V}, f=1\text{MHz}$		1060		pF
Output Capacitance	C_{oss}			180		pF
Reverse Transfer Capacitance	C_{rss}			135		pF
Turn-ON Delay Time	$t_d(on)$			17.5		ns
Rise Time	t_r	See specified Test Circuit.		120		ns
Turn-OFF Delay Time	$t_d(off)$			68		ns
Fall Time	t_f			80		ns
Total Gate Charge	Q_g			10.8		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=10\text{V}, V_{GS}=4.5\text{V}, I_D=7.5\text{A}$		2.1		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			2.9		nC
Diode Forward Voltage	V_{SD}		$I_S=7.5\text{A}, V_{GS}=0\text{V}$		0.74	1.2
[P-channel]						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=-1\text{mA}, V_{GS}=0\text{V}$	-20			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20\text{V}, V_{GS}=0\text{V}$			-1	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 8\text{V}, V_{DS}=0\text{V}$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=-10\text{V}, I_D=-1\text{mA}$	-0.4		-1.3	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=-10\text{V}, I_D=-3\text{A}$	4.9	8.3		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D=-3\text{A}, V_{GS}=-4.5\text{V}$		29	38	$\text{m}\Omega$
	$R_{DS(on)2}$	$I_D=-1.5\text{A}, V_{GS}=-2.5\text{V}$		41	58	$\text{m}\Omega$
	$R_{DS(on)3}$	$I_D=-0.5\text{A}, V_{GS}=-1.8\text{V}$		64	98	$\text{m}\Omega$
Input Capacitance	C_{iss}	$V_{DS}=-10\text{V}, f=1\text{MHz}$		960		pF
Output Capacitance	C_{oss}			180		pF
Reverse Transfer Capacitance	C_{rss}			140		pF
Turn-ON Delay Time	$t_d(on)$			14		ns
Rise Time	t_r	See specified Test Circuit.		55		ns
Turn-OFF Delay Time	$t_d(off)$			92		ns
Fall Time	t_f			68		ns
Total Gate Charge	Q_g			11		nC
Gate-to-Source Charge	Q_{gs}	$V_{DS}=-10\text{V}, V_{GS}=-4.5\text{V}, I_D=-5\text{A}$		2.0		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			2.8		nC
Diode Forward Voltage	V_{SD}		$I_S=-5\text{A}, V_{GS}=0\text{V}$		-0.82	-1.2

Switching Time Test Circuit

[N-channel]

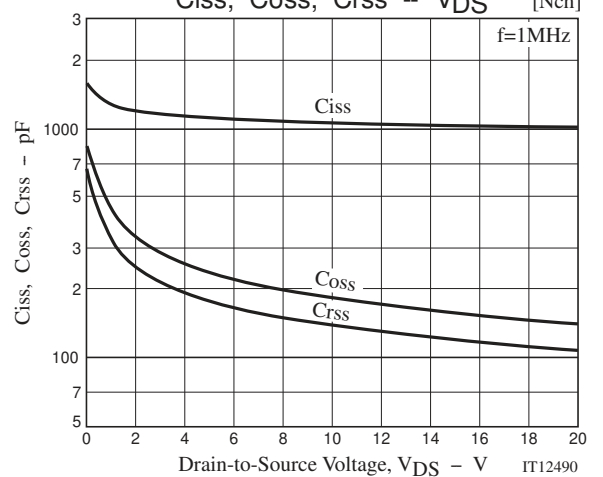
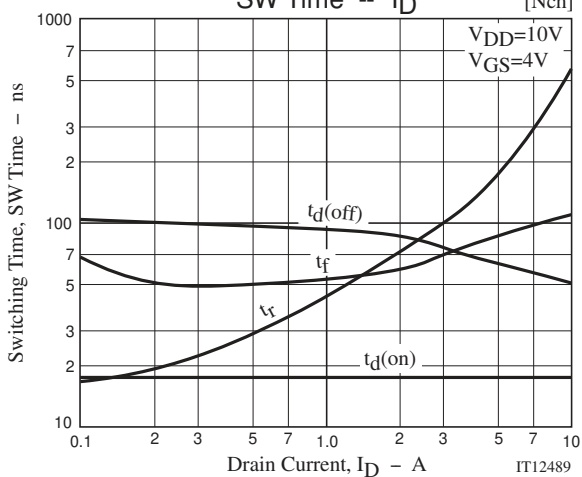
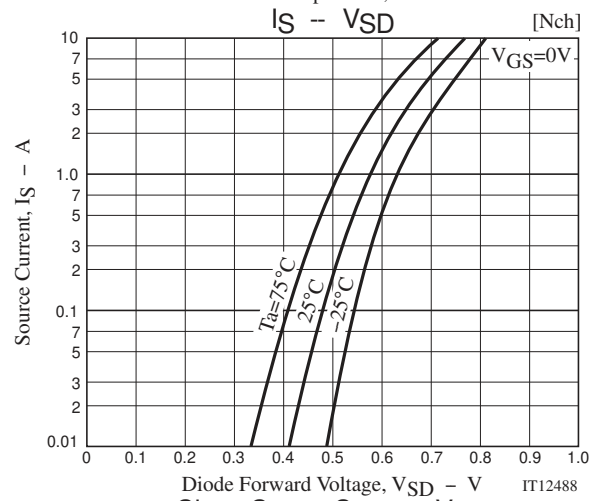
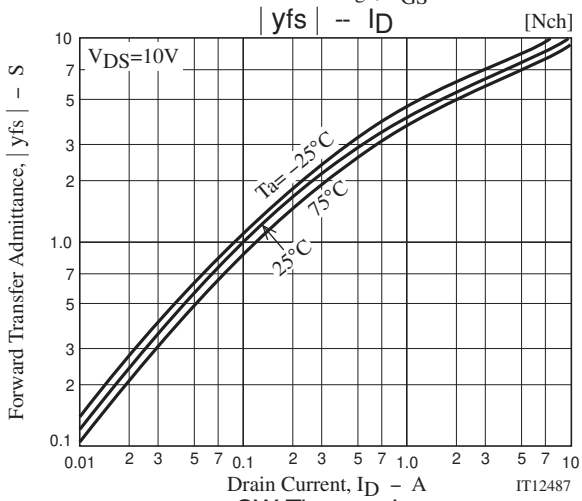
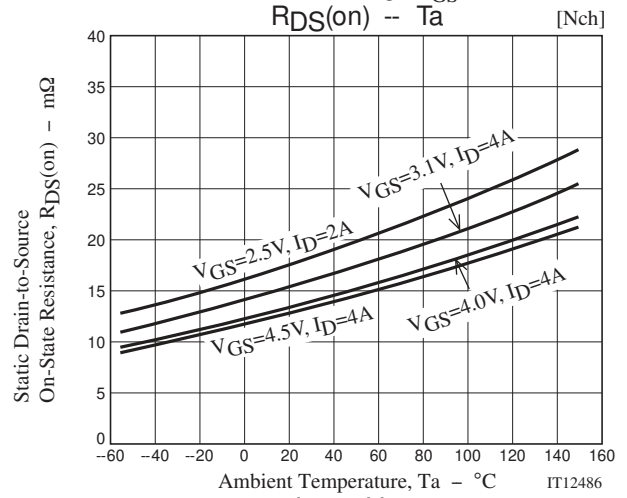
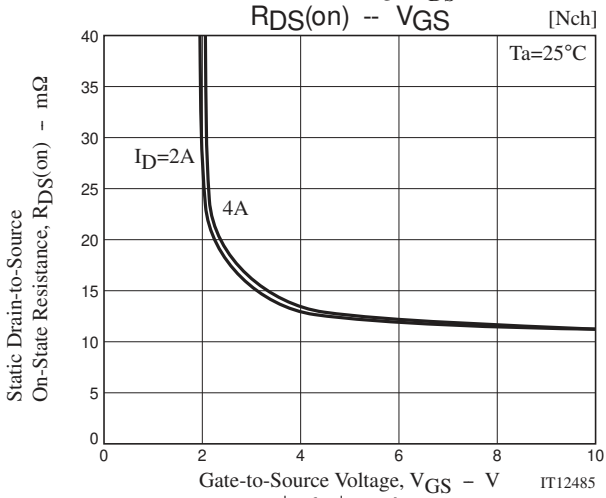
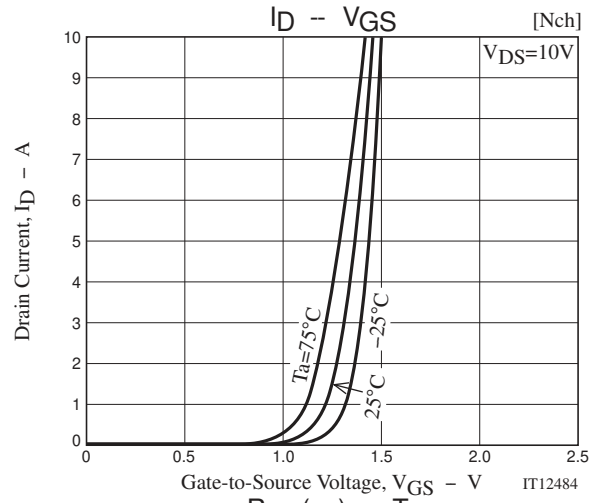
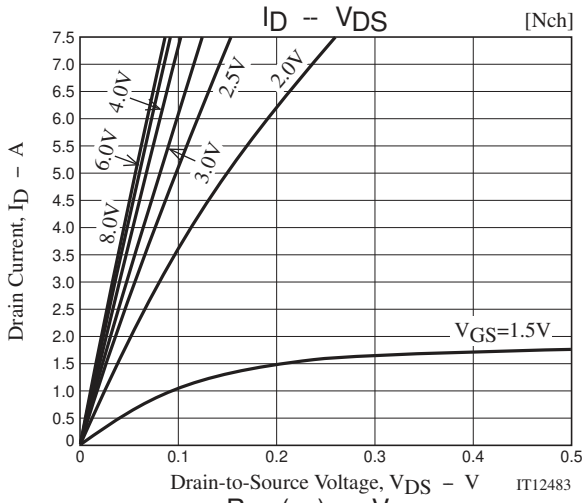


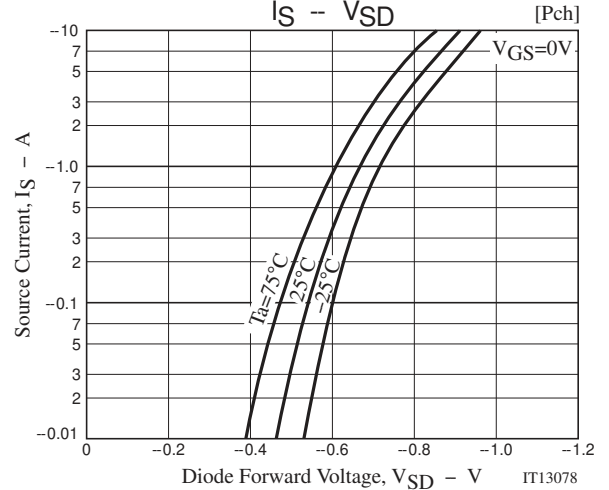
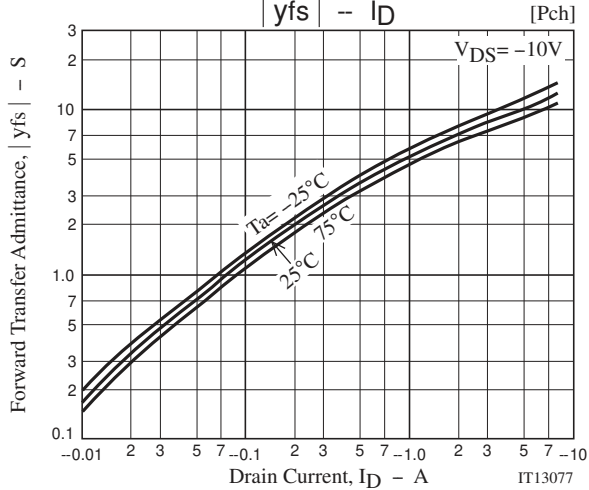
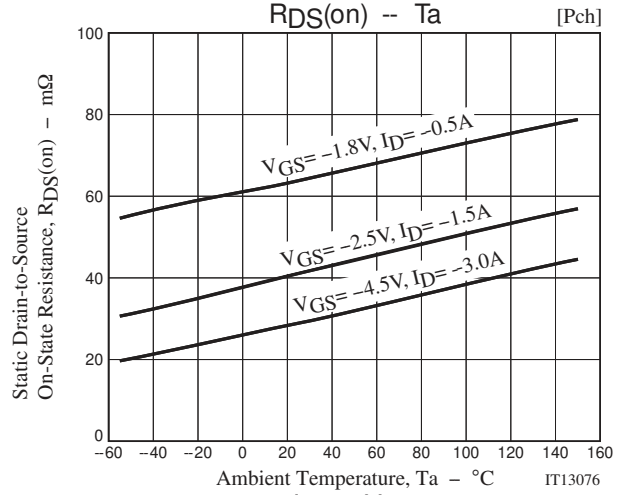
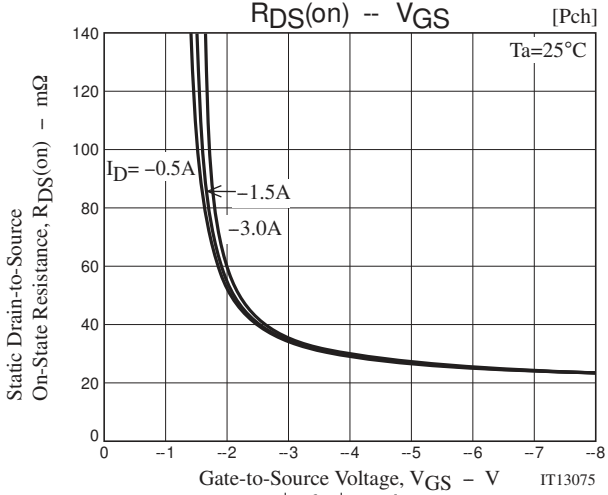
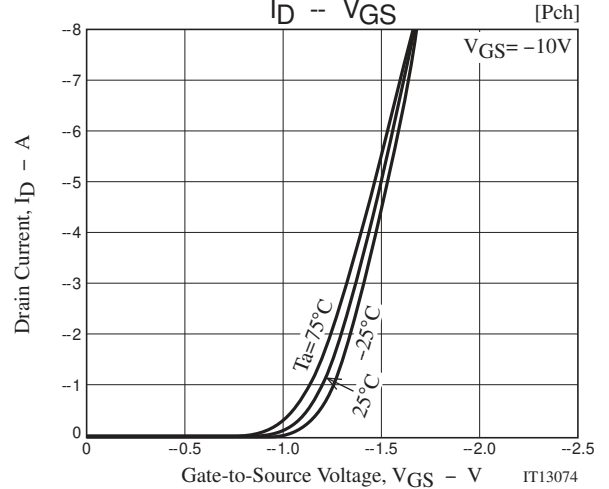
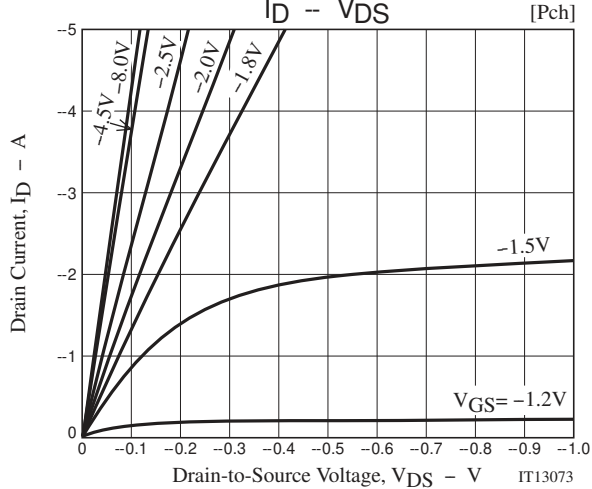
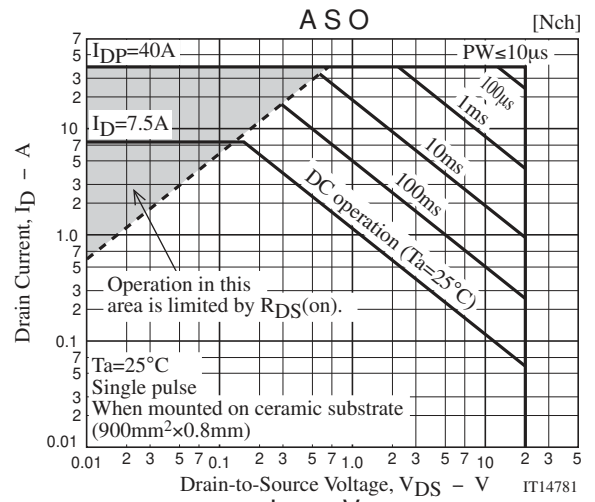
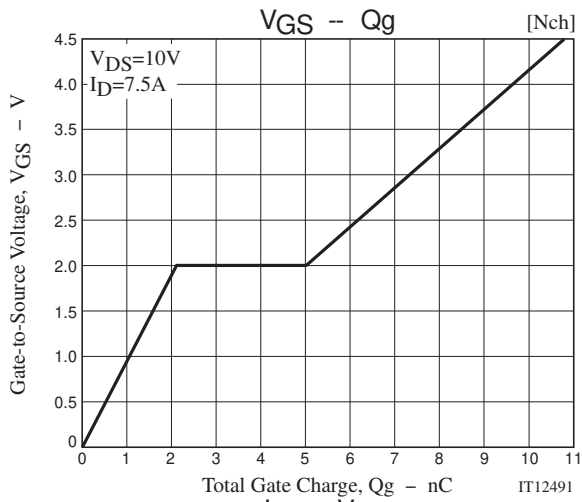
[P-channel]

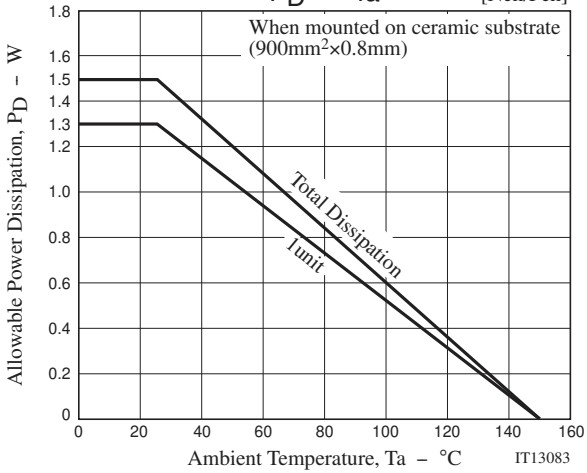
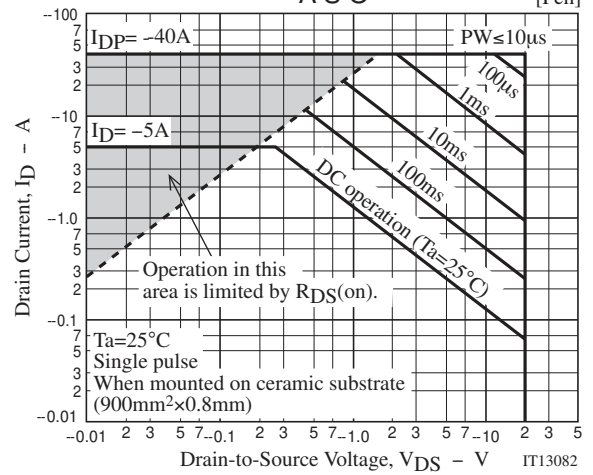
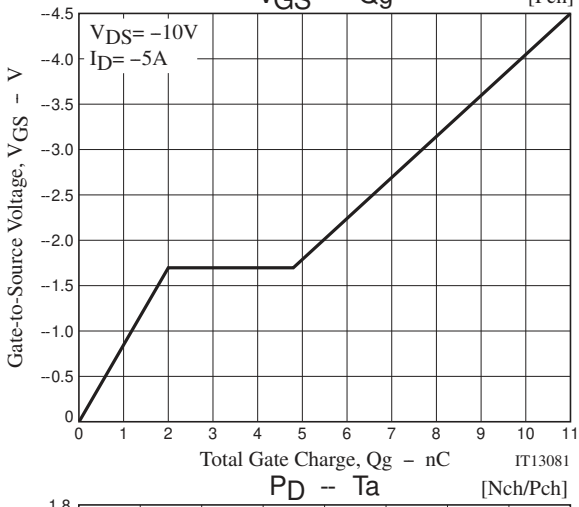
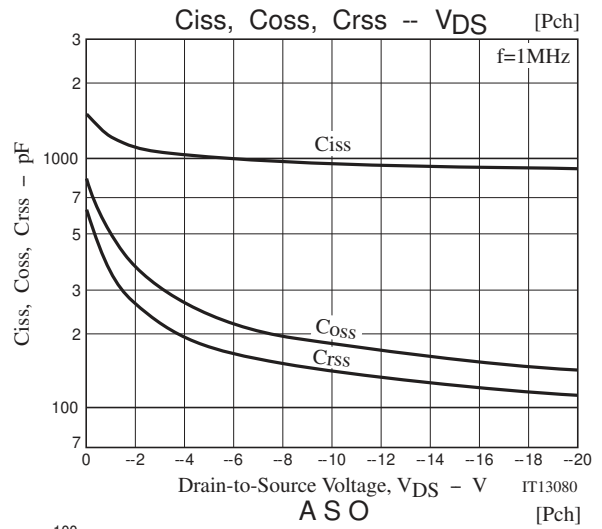
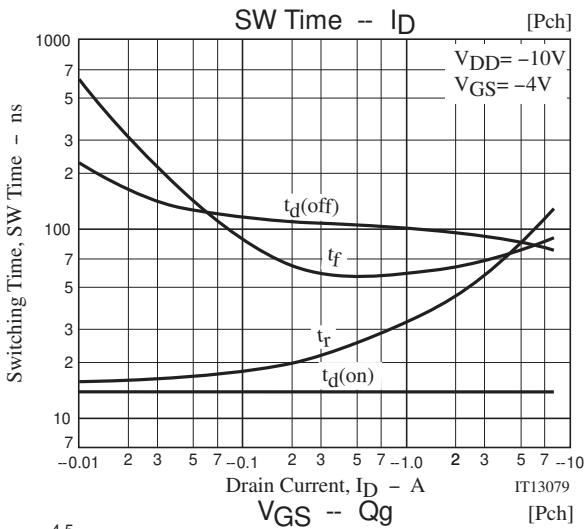


Ordering Information

Device	Package	Shipping	memo
ECH8668-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free







Embossed Taping Specification

ECH8668-TL-H

1. Packing Format

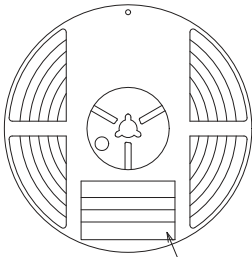
Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
ECH8	CPH6	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Reel label, Inner box label
(unit :mm)

Outer box label

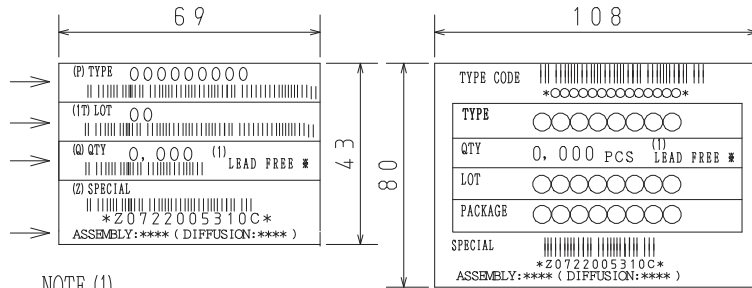
It is a label at the time of factory shipments.
The form of a label may change in physical distribution process.

Packing method



Reel label

Type No.
LOT No.
Quantity
Origin



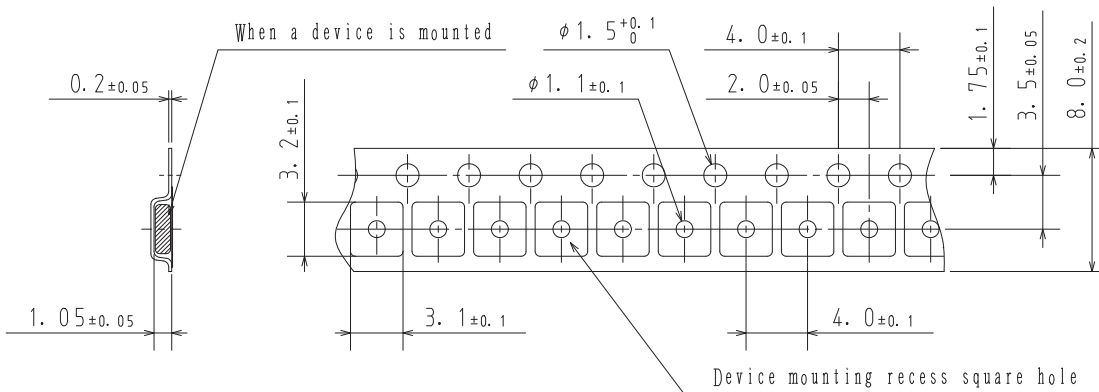
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

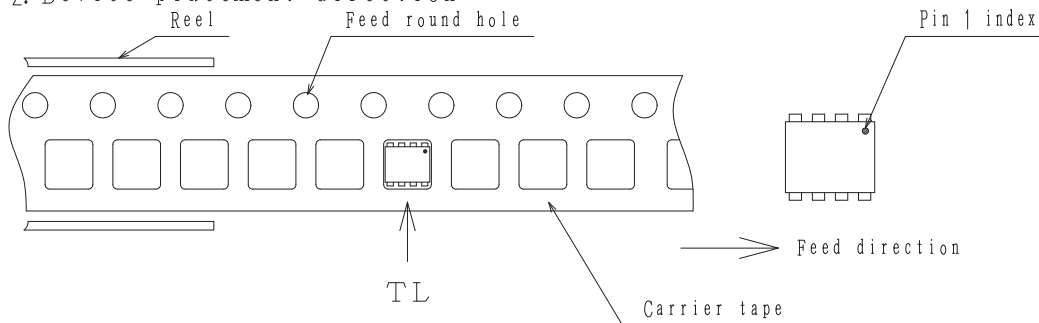
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction

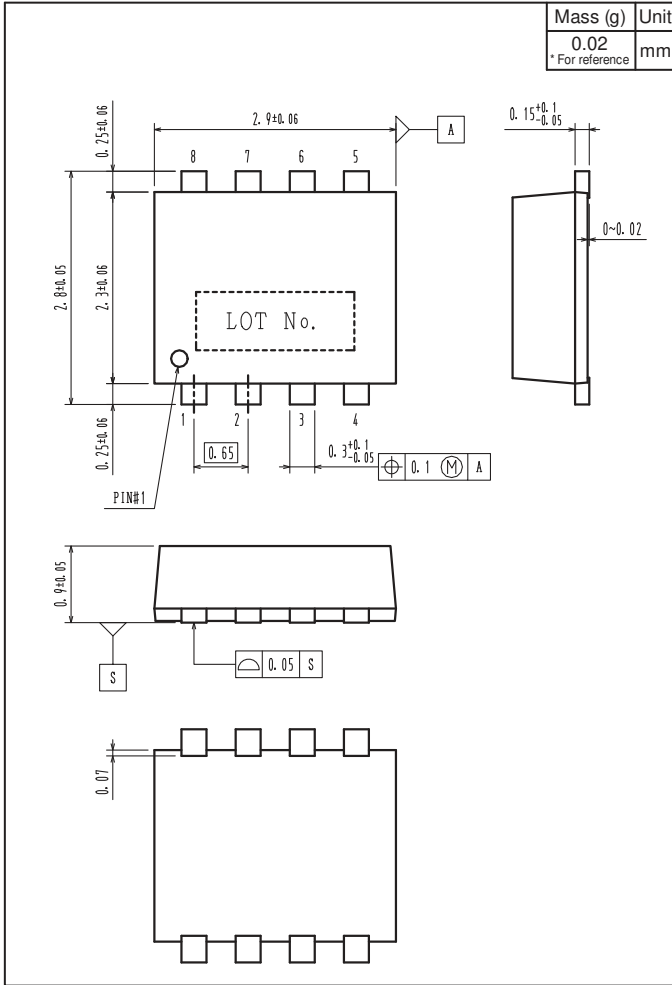


Those with pin 1 index on the feed hole side.....TL

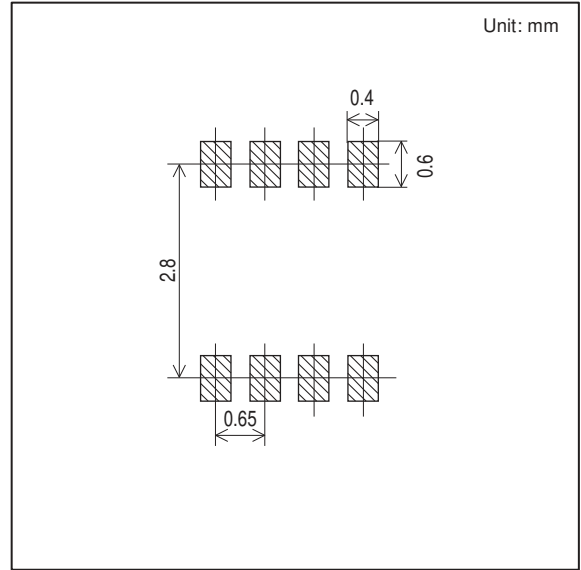
ECH8668

Outline Drawing

ECH8668-TL-H



Land Pattern Example



Note on usage : Since the ECH8668 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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